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			Application Number	Unknown	
			Confirmation Number	Unknown	
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			First Named Inventor	Risho KOH	
			Art Unit	Unknown	
			Examiner Name	Unknown	
Sheet	1	of	1	Attorney Docket Number	Q76865

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
TZ		US 2002/0185687	A1	12-12-2002	NEC Corporation
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>2</sup>	Number <sup>4</sup>	Kind Code <sup>3</sup> (if known)			
TZ		JP	4-34980	A	02-05-1992	Mitsubishi Electric Corp.	Abstract
		JP	2000-294794	A	10-20-2000	Hitachi Ltd.	Abstract
		JP	2002-217420	A	08-02-2002	Samsung Electronics Co., Ltd.	Abstract
		JP	11-135795	A	05-21-1999	NEC Corp.	Abstract
		JP	2001-024202	A	01-26-2001	Hyundai Electronics Ind. Co., Ltd.	Abstract
		WO	03/023865	A1	03-20-2003	NEC Corp.	Abstract
		JP	2000-332250	A	11-30-2000	Sony Corp.	Abstract
TZ		JP	2000-252471	A	09-14-2000	NEC Corp.	Abstract

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
TZ		KOH et al., "Body-Contacted SOI MOSFET Structure with Fully Bulk CMOS Compatible Layout and Process", <i>IEEE Electron Device Letters</i> , Vol. 18, No. 3, March 1997, pp. 102-104	
		CHEN et al., "Suppression of the SOI Floating-body Effects by Linked-body Device Structure", <i>1996 Symposium on VLSI Technology Digest of Technical Papers</i> , June 11-13, 1996, pp. 92-93	
		MAEDA et al., "Impact of 0.18μm SOI CMOS Technology using Hybrid Trench Isolation with High Resistivity Substrate on Embedded RF/Analog Applications", <i>2000 Symposium on VLSI Technology Digest of Technical Papers</i> , June 13-15, 2000, pp. 154-155	
TZ		YAMAGAMI et al., "Thin Film SOI-MOSFET with Body Contact Structure using Elevated Field Insulator", <i>The Japan Society of Applied Physics, The 63<sup>rd</sup> Autumn Meeting, 2002</i> , September 24, 2002, pp. 801, with English translation	

Examiner Signature		Date Considered	03/01/05
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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